

TOSHIBA Photocoupler GaAs Ired &amp; Photo-Transistor

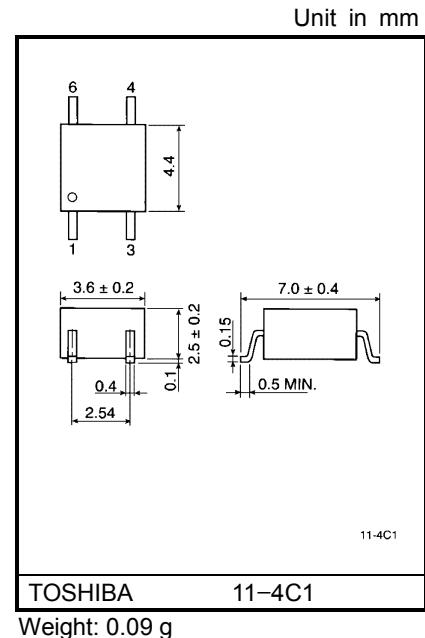
# **TLP180**

Programmable Controllers  
AC / DC-Input Module  
Telecommunication

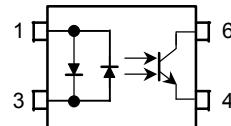
The TOSHIBA mini flat coupler TLP180 is a small outline coupler, suitable for surface mount assembly.

TLP180 consist of a photo transistor, optically coupled to a gallium arsenide infrared emitting diode connected inverse parallel, and can operate directly by AC input current.

- Collector-emitter voltage: 80 V (min.)
- Current transfer ratio: 50% (min.)  
Rank GB: 100% (min.)
- Isolation voltage: 3750Vrms (min.)
- UL recognized: UL1577, file No. E67349



## **Pin Configuration (top view)**



- 1: Anode, Cathode
- 3: Cathode, Anode
- 4: Emitter
- 6: Collector

**Maximum Ratings (Ta = 25°C)**

Characteristic		Symbol	Rating	Unit
LED	Forward current	I <sub>F(RMS)</sub>	±50	mA
	Forward current derating (Ta≥53°C)	ΔI <sub>F</sub> / °C	-0.7	mA / °C
	Pulse forward current (Note1)	I <sub>FP</sub>	±1	A
	Junction temperature	T <sub>j</sub>	125	°C
Detector	Collector-emitter voltage	V <sub>CEO</sub>	80	V
	Emitter-collector voltage	V <sub>ECO</sub>	7	V
	Collector current	I <sub>C</sub>	50	mA
	Power dissipation	P <sub>C</sub>	150	mW
	Power dissipation derating (Ta ≥ 25°C)	ΔP <sub>C</sub> / °C	-1.5	mW / °C
	Junction temperature	T <sub>j</sub>	125	°C
Storage temperature range		T <sub>stg</sub>	-55~125	°C
Operating temperature range		T <sub>opr</sub>	-55~100	°C
Lead soldering temperature(10s)		T <sub>sol</sub>	260	°C
Total package power dissipation		P <sub>T</sub>	200	mW
Total package power dissipation derating (Ta ≥ 25°C)		ΔP <sub>T</sub> / °C	-2.0	mW / °C
Isolation voltage (AC,1min.,R.H. ≤ 60%) (Note 2)		BV <sub>S</sub>	3750	Vrms

Note 1: Pulse width ≤ 100μs, f=100Hz

Note 2: Device considered a two terminal device: Pins 1 and 3 shorted together and 4 and 6 shorted together.

**Recommended Operating Conditions**

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Supply voltage	V <sub>CC</sub>	—	5	48	V
Forward current	I <sub>F(RMS)</sub>	—	16	20	mA
Collector current	I <sub>C</sub>	—	1	10	mA
Operating temperature	T <sub>opr</sub>	-25	—	85	°C

Electrical Characteristics ( $T_a = 25^\circ\text{C}$ )

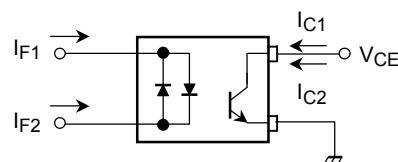
Characteristic		Symbol	Test Condition	Min.	Typ.	Max.	Unit
LED	Forward voltage	$V_F$	$I_F = \pm 10 \text{ mA}$	1.0	1.15	1.3	V
	Capacitance	$C_T$	$V = 0, f = 1 \text{ MHz}$	—	60	—	pF
Detector	Collector-emitter breakdown voltage	$V_{(\text{BR}) \text{ CEO}}$	$I_C = 0.5 \text{ mA}$	80	—	—	V
	Emitter-collector breakdown voltage	$V_{(\text{BR}) \text{ ECO}}$	$I_E = 0.1 \text{ mA}$	7	—	—	V
	Collector dark current	$I_{\text{CEO}}$	$V_{CE} = 48 \text{ V}$ (ambient light below $1000 \text{ Lx}$ ) (Note3)	—	0.01 (2)	0.1 (10)	$\mu\text{A}$
			$V_{CE} = 48 \text{ V}$ (ambient light $T_a = 85^\circ\text{C}$ below $1000 \text{ Lx}$ ) (Note3)	—	2 (4)	50 (50)	$\mu\text{A}$
	Capacitance (collector to emitter)	$C_{CE}$	$V = 0, f = 1 \text{ MHz}$	—	10	—	pF

Note 3: Please use standard electric lamp to light up the device's marking surface.

Coupled Electrical Characteristics ( $T_a = 25^\circ\text{C}$ )

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Current transfer ratio	$I_C / I_F$	$I_F = \pm 5 \text{ mA}, V_{CE} = 5 \text{ V}$ Rank GB	50	—	600	%
			100	—	600	
Saturated CTR	$I_C / I_F (\text{sat})$	$I_F = \pm 1 \text{ mA}, V_{CE} = 0.4 \text{ V}$ Rank GB	—	60	—	%
			30	—	—	
Collector-emitter saturation voltage	$V_{CE} (\text{sat})$	$I_C = 2.4 \text{ mA}, I_F = \pm 8 \text{ mA}$	—	—	0.4	V
		$I_C = 0.2 \text{ mA}, I_F = \pm 1 \text{ mA}$ Rank GB	—	0.2	—	
		—	—	—	0.4	
Off-state collector current	$I_{C(\text{off})}$	$V_F = \pm 0.7 \text{ V}, V_{CE} = 48 \text{ V}$	—	1	10	$\mu\text{A}$
CTR symmetry	$I_C (\text{ratio})$	$I_C (I_F = -5 \text{ mA}) / I_C (I_F = 5 \text{ mA})$ (Note4)	0.33	1	3	—

$$\text{Note 4 : } I_C(\text{ratio}) = \frac{I_C(2)(I_F = I_F2, V_{CE} = 5V)}{I_C(1)(I_F = I_F1, V_{CE} = 5V)}$$



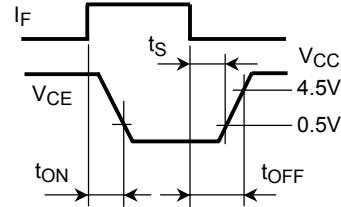
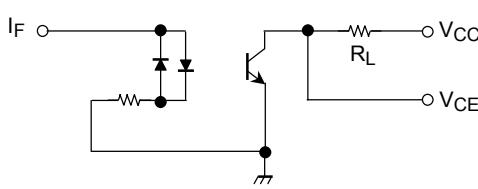
**Isolation Characteristics (Ta = 25°C)**

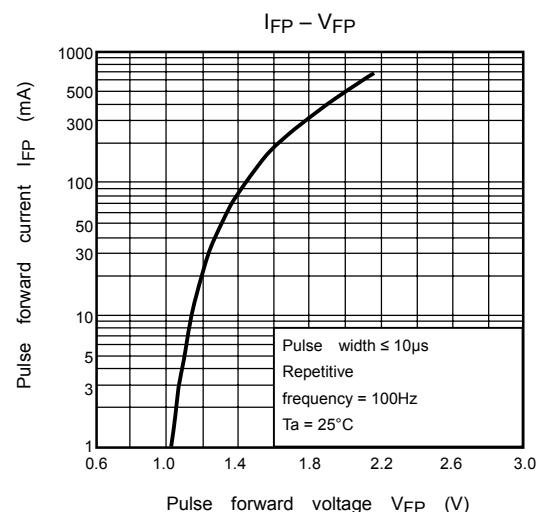
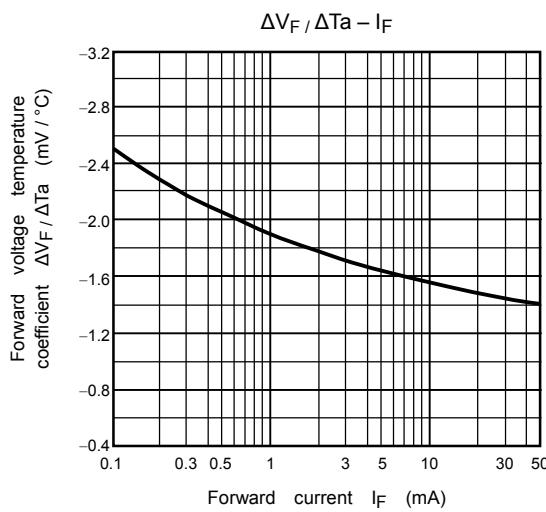
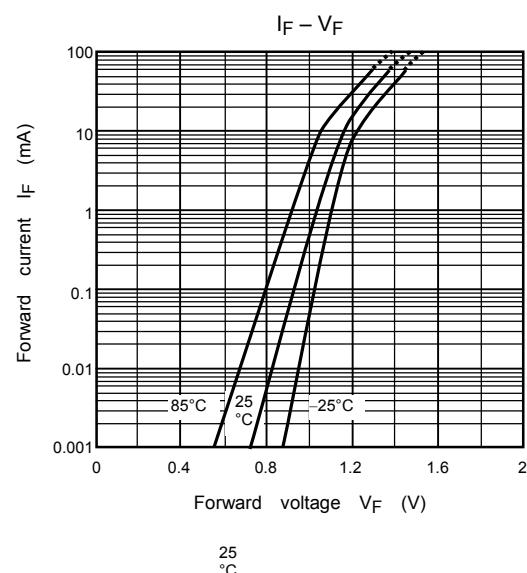
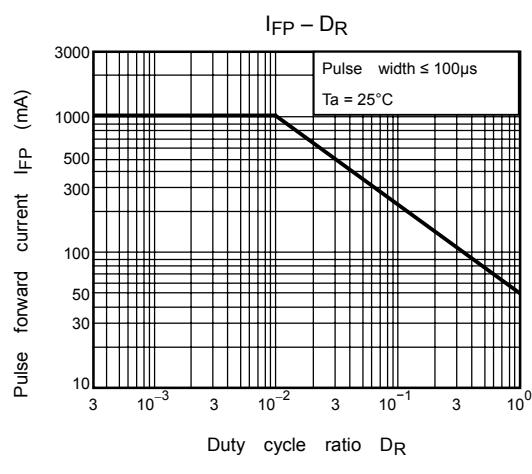
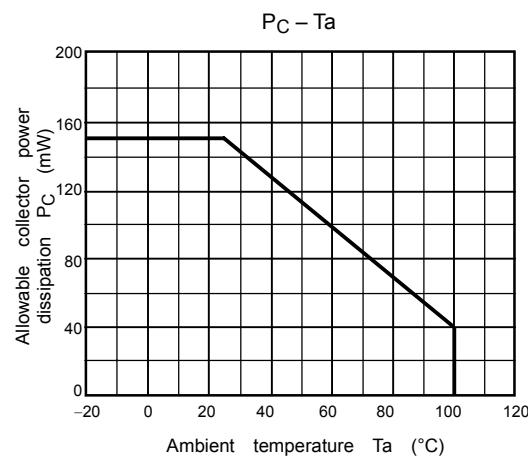
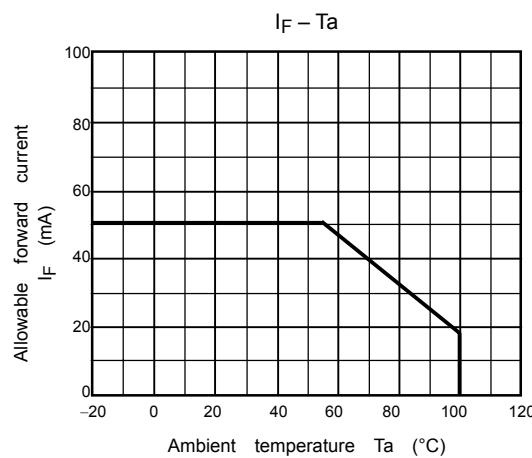
Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Capacitance input to output	C <sub>S</sub>	V <sub>S</sub> = 0V, f = 1 MHz	—	0.8	—	pF
Isolation resistance	R <sub>S</sub>	V <sub>S</sub> = 500 V, R.H. ≤ 60%	5×10 <sup>10</sup>	10 <sup>14</sup>	—	Ω
Isolation voltage	BVS	AC, 1 minute	3750	—	—	V <sub>rms</sub>
		AC, 1 second, in oil	—	10000	—	
		DC, 1 minute, in oil	—	10000	—	V <sub>dc</sub>

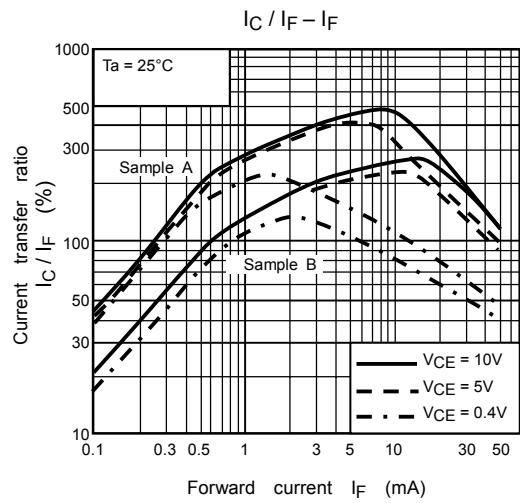
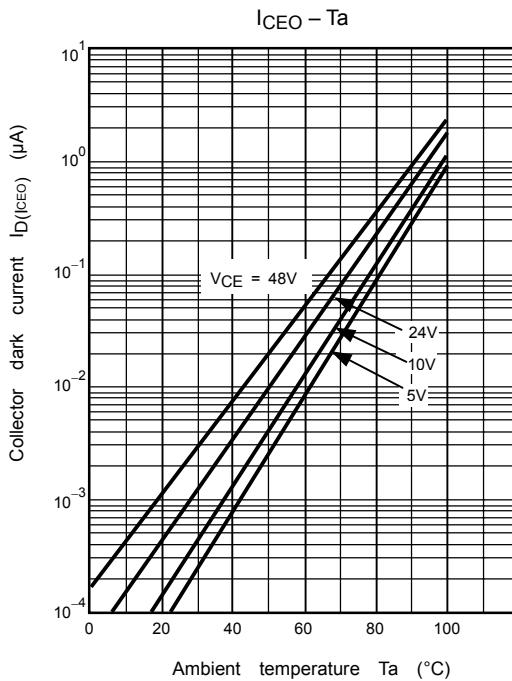
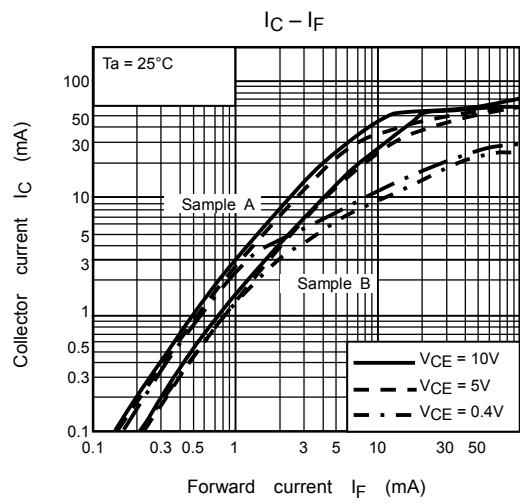
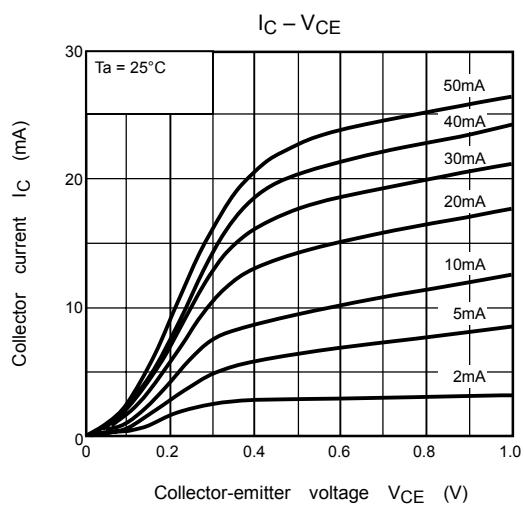
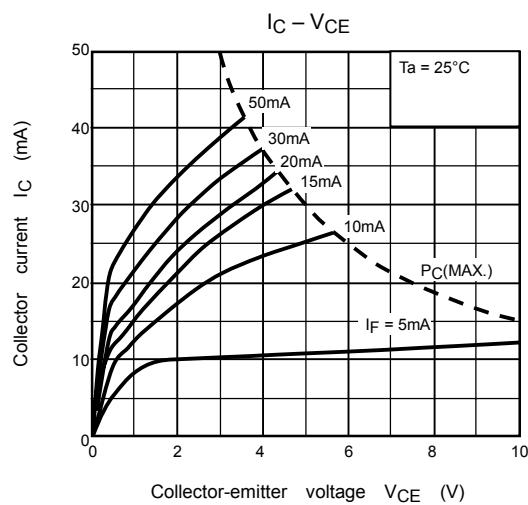
**Switching Characteristics (Ta = 25°C)**

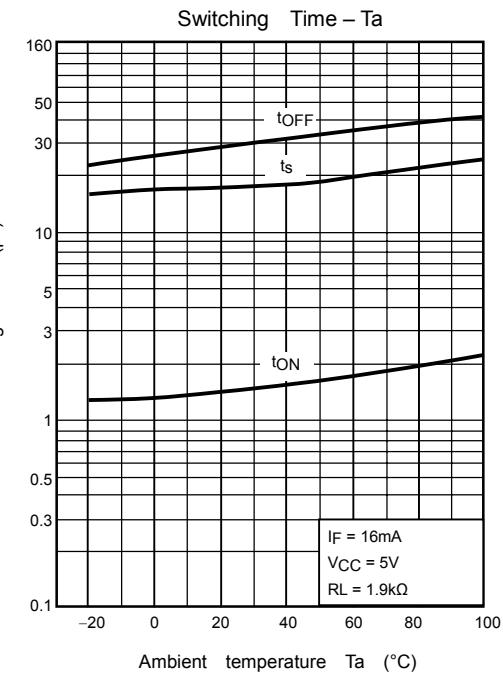
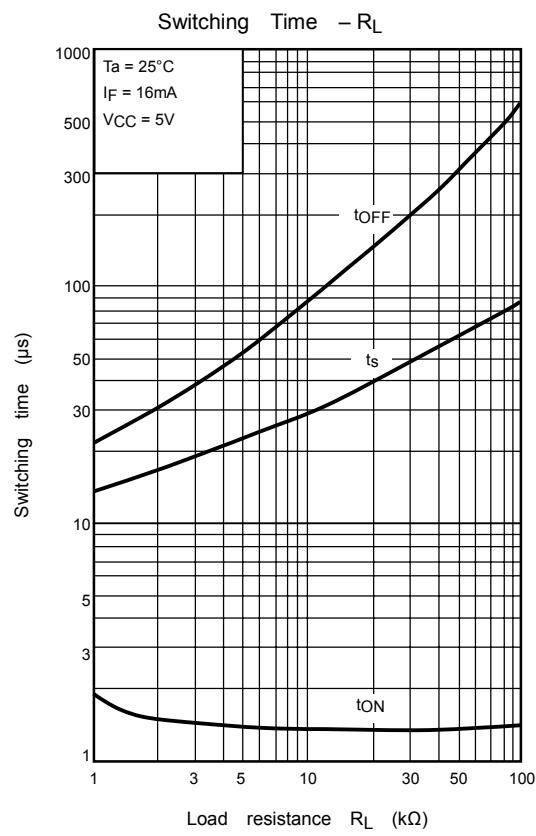
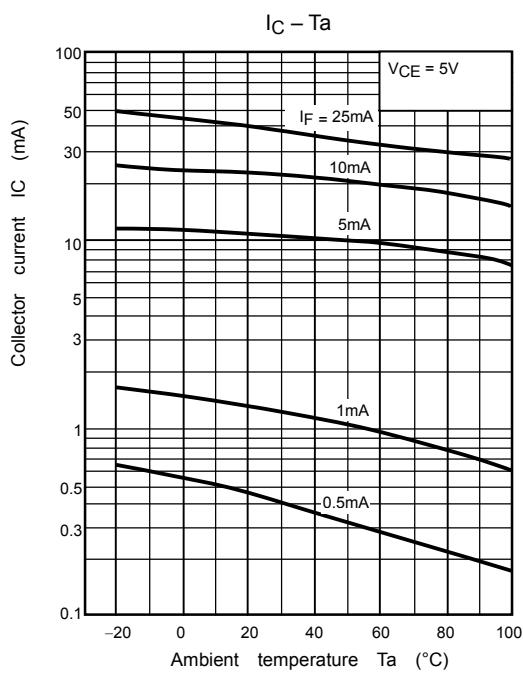
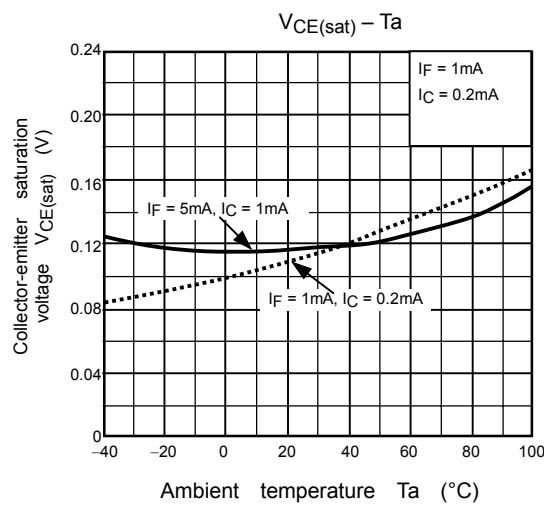
Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Rise time	t <sub>r</sub>	V <sub>CC</sub> = 10 V, I <sub>C</sub> = 2 mA R <sub>L</sub> = 100Ω	—	2	—	μs
Fall time	t <sub>f</sub>		—	3	—	
Turn-on time	t <sub>on</sub>		—	3	—	
Turn-off time	t <sub>off</sub>		—	3	—	
Turn-on time	t <sub>ON</sub>	R <sub>L</sub> = 1.9 kΩ V <sub>CC</sub> = 5 V, I <sub>F</sub> = ±16 mA (Fig.1)	—	2	—	μs
Storage time	t <sub>s</sub>		—	25	—	
Turn-off time	t <sub>OFF</sub>		—	40	—	

Fig. 1: Switching time test circuit









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